

isc Silicon PNP Darlington Power Transistor

BD652F

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -100V(\text{Min})$
- High DC Current Gain
- Low Saturation Voltage
- Complement to Type BD651F
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

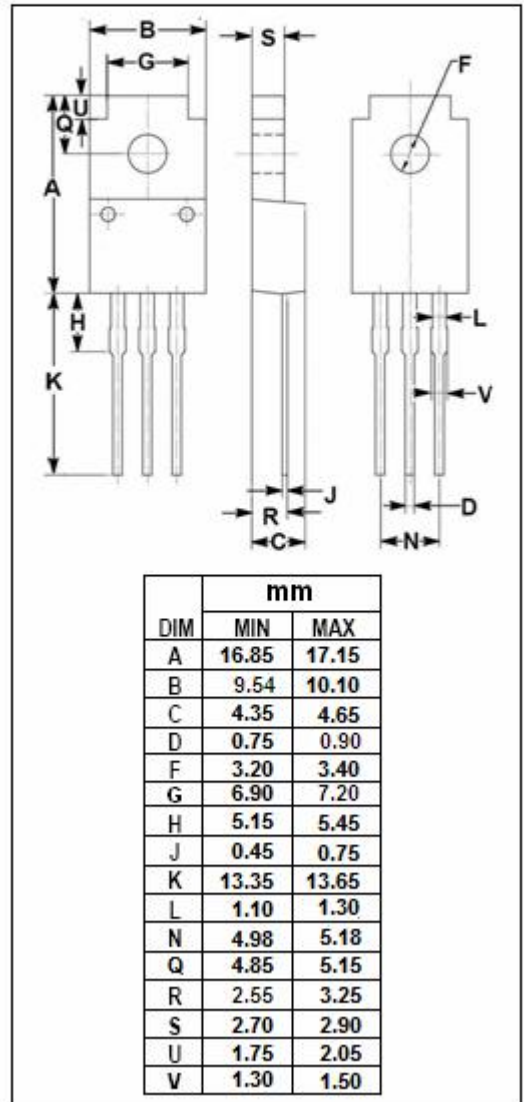
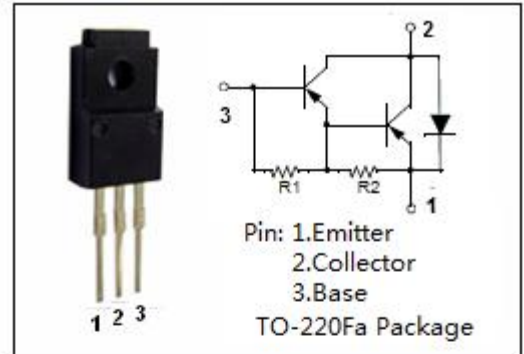
- Designed for use as complementary AF push-pull output stage applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-8	A
I_{CP}	Collector Current-Peak	-12	A
I_B	Base Current-Continuous	-0.15	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	20	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	32	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.6	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	6.3	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}; I_B = 0$	-120			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -3\text{A}; I_B = -12\text{mA}$			-2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -50\text{mA}$			-2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -50\text{mA}$			-3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -3\text{A}; V_{CE} = -3\text{V}$			-2.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -120\text{V}; I_E = 0$			-0.1	mA
		$V_{CB} = -70\text{V}; I_E = 0; T_C = 150^{\circ}\text{C}$			-1.0	
I_{CEO}	Collector Cutoff Current	$V_{CE} = -60\text{V}; I_B = 0$			-0.5	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-5	mA
h_{FE-1}	DC Current Gain	$I_C = -0.5\text{A}; V_{CE} = -3\text{V}$		2700		
h_{FE-2}	DC Current Gain	$I_C = -3\text{A}; V_{CE} = -3\text{V}$	750			
h_{FE-3}	DC Current Gain	$I_C = -8\text{A}; V_{CE} = -3\text{V}$		2000		

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